



DC COMPONENTS CO., LTD.

DISCRETE SEMICONDUCTORS

2N3773

TECHNICAL SPECIFICATIONS OF NPN EPITAXIAL PLANAR TRANSISTOR

Description

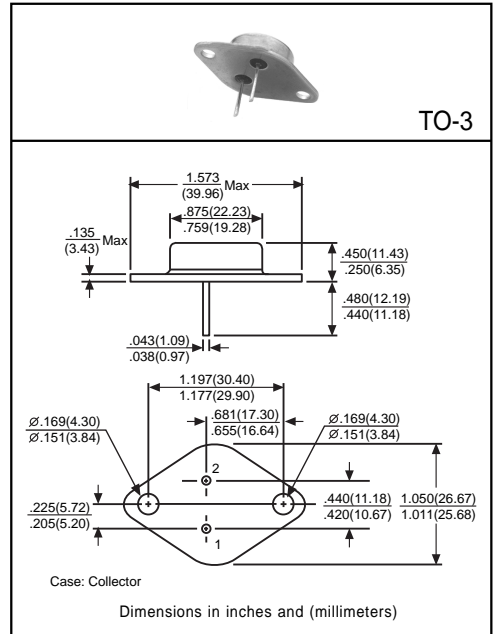
Designed for high power audio, disk head positioners, and other linear applications.

Pinning

1 = Base  
2 = Emitter  
Case = Collector

Absolute Maximum Ratings (TA=25°C)

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	V <sub>CB0</sub>	160	V
Collector-Emitter Voltage	V <sub>CEO</sub>	140	V
	V <sub>CEx</sub>	160	V
Emitter-Base Voltage	V <sub>EBO</sub>	7	V
Collector Current (continuous)	I <sub>C</sub>	16	A
Collector Current (peak)	I <sub>C</sub>	30	A
Total Power Dissipation (T <sub>C</sub> =25°C)	P <sub>D</sub>	150	W
Junction Temperature	T <sub>J</sub>	+200	°C
Storage Temperature	T <sub>STG</sub>	-65 to +200	°C



Electrical Characteristics

(Ratings at 25°C ambient temperature unless otherwise specified)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Conditions
Collector-Emitter Sustaining Voltage	V <sub>CEO(sus)</sub>	140	-	-	V	I <sub>C</sub> =0.2A, I <sub>B</sub> =0
	V <sub>CEx(sus)</sub>	160	-	-	V	I <sub>C</sub> =0.1A, V <sub>BE(off)</sub> =1.5V, R <sub>BE</sub> =100Ω
	V <sub>CEr(sus)</sub>	150	-	-	V	I <sub>C</sub> =0.1A, R <sub>BE</sub> =100Ω
Collector Cutoff Current	I <sub>CEO</sub>	-	-	10	mA	V <sub>CE</sub> =120V, I <sub>B</sub> =0
	I <sub>CEx</sub>	-	-	2	mA	V <sub>CE</sub> =140V, V <sub>BE(off)</sub> =1.5V
		-	-	10	mA	V <sub>CE</sub> =140V, V <sub>BE(off)</sub> =1.5V, T <sub>C</sub> =150°C
	I <sub>CB0</sub>	-	-	2	mA	V <sub>CB</sub> =140V, I <sub>E</sub> =0
Emitter Cutoff Current	I <sub>EBO</sub>	-	-	5	mA	V <sub>BE</sub> =7V, I <sub>C</sub> =0
Collector-Emitter Saturation Voltage <sup>(1)</sup>	V <sub>CE(sat)1</sub>	-	-	1.4	V	I <sub>C</sub> =8A, I <sub>B</sub> =0.8A
	V <sub>CE(sat)2</sub>	-	-	4	V	I <sub>C</sub> =16A, I <sub>B</sub> =3.2A
Base-Emitter On Voltage <sup>(1)</sup>	V <sub>BE(on)</sub>	-	-	2.2	V	I <sub>C</sub> =8A, V <sub>CE</sub> =4V
DC Current Gain <sup>(1)</sup>	h <sub>FE1</sub>	15	-	60	-	I <sub>C</sub> =8A, V <sub>CE</sub> =4V
	h <sub>FE2</sub>	5	-	-	-	I <sub>C</sub> =16A, V <sub>CE</sub> =4V
Second Breakdown Collector with Base Forward Bias	I <sub>s/b</sub>	1.5	-	-	A	V <sub>CE</sub> =100V, t=1.0s, Non-repetitive
Small-Signal Current Gain	h <sub>fe</sub>	40	-	-	-	I <sub>C</sub> =1A, V <sub>CE</sub> =4V, f=1KHZ
Magnitude of Common-Emitter Small-Signal, Short-Circuit, Forward Current Transfer Ratio	h <sub>fe</sub>	4	-	-	-	I <sub>C</sub> =1A, f=50KHZ

(1)Pulse Test: Pulse Width ≤300μs, Duty Cycle ≤2%